

Search Notes

L Number	Hits	Search Text	DB	Time stamp
-	3	("6613653").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 19:18
-	3	("6339013").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 19:20
-	482	(438/682).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 19:59
-	626	(438/683).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 19:59
-	514	(438/597).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 20:00
-	7696	polysilicon and amorphous and anneal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 20:00
-	4111	polysilicon and amorphous same anneal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 20:00
-	3259	polysilicon and amorphous with silicon same anneal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 20:01
-	828	polysilicon and amorphous with silicon same anneal\$3 and ("200" or "300" or "400" or "500") with temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 20:02
-	208	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 20:03
-	171	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature and metal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 20:04
-	113	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature and aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 21:20
-	5	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature same aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 21:06
-	1		USPAT	2004/05/31 21:04

-	256	"5275851"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 21:07
-	226	"5275851" and aluminum and amorphous adj silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 21:09
-	55	"5275851" and aluminum same amorphous adj silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 21:09
-	23	"5275851" and aluminum same amorphous adj silicon same anneal\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 21:20
-	16	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature and aluminum same crystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 21:23
-	11	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature same metal same crystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 23:56
-	21	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature and mic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 00:08
-	26	amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature and mic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 00:08
-	8	amorphous with silicon same anneal\$3 with temperature and mic same al	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 00:09
-	57	amorphous with silicon same anneal\$3 with temperature and mic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 00:12
-	87	amorphous with silicon same anneal\$3 and mic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 00:14
-	625	amorphous with silicon same anneal\$3 and metal with crystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 00:51
-	77	amorphous with silicon same anneal\$3 and metal near crystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 00:15
-	87	amorphous with silicon same anneal\$3 and mic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 02:40

1	432	(438/486).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 02:40
2	729	(438/482).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/01 02:40